# DS89LV21 3V Differential CMOS Line Driver and Receiver Pair

#### **General Description**

The DS89LV21 is a differential CMOS line driver and receiver pair, designed to operate with TIA/EIA-422-B (RS-422) and V.11 electrical characteristics interface standards. The DS89LV21 provides one driver and one receiver in a minimum footprint. The device is featured in 8-pin SOIC and DIP packages.

The 3V CMOS design minimizes the supply current to 1.8 mA, making the device ideal for use in battery powered or power conscious applications.

The driver features a fast transition time specified at 3 ns, and a maximum differential skew of 2 ns making the driver ideal for use in high speed applications operating above 5 MHz.

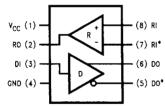
The receiver can detect signals as low as 200 mV, and also incorporates hysteresis for noise rejection. Skew is specified at 4 ns maximum.

The DS89LV21 is compatible with TTL and CMOS levels (DI and RO).

#### **Features**

- Single 3.3V power supply operation
- Operates with TIA/EIA-422-B (RS-422) and ITU V.11
- LOW POWER design—6 mW typical
- Guaranteed AC parameters:
  - Maximum driver skew 2.0 ns
  - Maximum receiver skew 4.0 ns
- Extended temperature range -40°C to +85°C
- Available in SOIC packaging
- Operates over 10 Mbps
- Receiver OPEN† input failsafe feature

# **Connection Diagram**



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Order Number DS89LV21TM or DS89LV21TN See NS Package Number M08A or N08E

# **Truth Tables**

#### Driver

Input	Outputs				
DI	DO	DO*			
Н	Н	L			
L	L	н			

#### Receiver

Inputs	Output
RI-RI*	RO
V <sub>DiFF</sub> ≥ + 200 mV	Н
$V_{DIFF} \le -200  mV$	L
OPEN†	Н

†Non-terminated

#### Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V<sub>CC</sub>) Driver Input Voltage (DI) -1.5V to  $V_{CC} + 1.5V$ Driver Output Voltage (DO, DO\*) -0.5V to +7VReceiver Input Voltage-V<sub>CM</sub> (RI, RI\*) ±14V Differential Receiver Input ±14V Voltage-VDIF (RI, RI\*)

Receiver Output Voltage (RO)

-0.5V to  $V_{CC} + 0.5V$ Receiver Output Current (RO) ± 25 mA Storage Temperature Range (TSTG) -65°C to +150°C Lead Temperature (TL) +260°C

(Soldering 4 sec.)

Maximum Junction Tempera	iture 150°C
Maximum Package Power D	Dissipation @ +25°C
M Package	714 mW
N Package	1275 mV
Derate M Package	5.7 mW/°C above + 25°C
Derate N Package	10.2 mW/°C above +25°C

#### **Recommended Operating Conditions**

	Min	Max	Units
Supply Voltage (V <sub>CC</sub> )	3.0	3.6	٧
Operating Temperature (TA)	-40	+85	°C
Input Rise or Fall Time (DI)		500	ns

#### **Electrical Characteristics**

Over recommended supply voltage and operating temperature ranges, unless otherwise specified (Notes 2, 3)

Symbol	Parameter	Con	ditions	Pin	Min	Тур	Max	Units
DRIVER C	HARACTERISTICS							
V <sub>IH</sub>	Input Voltage HIGH				2.0		Vcc	V
V <sub>IL</sub>	Input Voltage LOW			<b>1</b> 5	GND		0.8	V
i <sub>IH</sub> , I <sub>IL</sub>	Input Current	VIN = VCC, GND	, 2.0V, 0.8V	DI		0.05	±10	μА
V <sub>CL</sub>	Input Clamp Voltage	I <sub>IN</sub> = -18 mA					-1.5	V
V <sub>OD1</sub>	Unloaded Output Voltage	No Load				2.6	4.0	V
V <sub>OD2</sub>	Differential Output Voltage	$R_L = 100\Omega$			1.2	1.6 ,		V
ΔV <sub>OD2</sub>	Change in Magnitude of V <sub>OD2</sub> for Complementary Output States					5.0	400	m∨
V <sub>OD3</sub>	Differential Output Voltage	$R_L = 150\Omega$		1.3	1.8		V	
V <sub>OD4</sub>	Differential Output Voltage	$R_L = 3.9  k\Omega$		DO,		2.3	4.0	V
Voc	Common Mode Voltage	$R_L = 100\Omega$		DO*		2.0	3.0	v
ΔV <sub>OC</sub>	Change in Magnitude of V <sub>OC</sub> for Complementary Output States					2.0	400	mV
losp	Output Short Circuit Current	V <sub>OUT</sub> = 0V			-30	-65	-100	mA
IOFF	Output Leakage Current	V <sub>CC</sub> = 0V	V <sub>OUT</sub> = +4V			0.03	+100	μΑ
			$V_{OUT} = -0.25V$			-0.08	-100	μA

#### **Electrical Characteristics**

Symbol	Parameter	Conditions			Pin	Min	Тур	Max	Units
RECEIVER	CHARACTERISTICS						1		
V <sub>TL</sub> , V <sub>TH</sub>	Differential Thresholds	$V_{IN} = +7V, 0V, -7V$			-200	±35	+200	mV	
V <sub>HYS</sub>	Hysteresis	V <sub>CM</sub> = 0V		7/			70	<del></del>	mV
R <sub>IN</sub>	Input Impedance	$V_{IN} = -7V, +7$	V, Other =	= 0V		6.5	8.5		kΩ
I <sub>iN</sub>	Input Current	Other Input = 0\		= +10V	RI,		+1.1	+ 1.5	mA
		V <sub>CC</sub> = 3.6V and	V <sub>IN</sub> =	= +3.0V	RI*	0	+0.27		mA
		V <sub>CC</sub> = 0V	V <sub>IN</sub> =	= +0.5V			-0.02		mA
	  -		V <sub>IN</sub> =	= -3V		0	-0.43		mA
			V <sub>IN</sub> =	= -10V			-1.25	-2.0	mA
$V_{OH}$	Output HIGH Voltage	$I_{OH} = -6 \text{ mA}$	V <sub>DIF</sub>	= + 1V	RO	2.4	3.0		٧
			V <sub>DIF</sub>	= OPEN		2.4	3.0		V
V <sub>OL</sub>	Output LOW Voltage	$I_{OL} = +6 \text{ mA}, V_{DIFF} = -1V$			ואט		0.08	0.3	V
Iosr	Output Short Circuit Current	V <sub>OUT</sub> = 0V			-15	-40	- 100	mA	
DRIVER AN	ID RECEIVER CHARACTERIS	TICS						-	
lcc	Supply Current	No Load	DI =	V <sub>CC</sub> or GND	Vcc		1.8	3	mA
			DI =	2.4V or 0.5V	VCC		2.0	6	mA
	hing Characteristic		ture range	es, unless othe	rwise s	pecified (	Note 3)		
Symbol	Parameter		Conditions			Min	Тур	Max	Units
DIFFEREN	FIAL DRIVER CHARACTERIST	rics							
				1					
t <sub>PLHD</sub>	Propagation Delay LOW to	HIGH RL =		(Figures 2,	3)	2	5.5	11	ns

t <sub>PHLD</sub>	Propagation Delay HIGH to LOW	GL = 50 pr		2	6.5	11	ns
tskD	Skew,  t <sub>PLHD</sub> -t <sub>PHLD</sub>		(Figures 2, 4)		1	2.0	лѕ
t <sub>TLH</sub>	Transition Time LOW to HIGH				3	6	ns
t <sub>THL</sub>	Transition Time HIGH to LOW				3	6	ns
RECEIVER	CHARACTERISTICS	T	<b>-</b>				
t <sub>PLH</sub>	Propagation Delay LOW to HIGH	$C_L = 50 \text{ pF}$ $V_{DIFF} = 2.5V$ $V_{CM} = 0V$	V <sub>DIFF</sub> = 2.5V	10	27	45	ns
t <sub>PHL</sub>	Propagation Delay HIGH to LOW			10	26	45	ns
tsk	Skew, t <sub>PLH</sub> -t <sub>PHL</sub>				1	4.0	ns
t <sub>r</sub>	Rise Time		(Figure 7)		3	6	ns
t <sub>4</sub>	Fall Time					T	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" specify conditions for device operation.

Note 2: Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground unless otherwise specified.

Note 3: All typicals are given for  $V_{CC} = 3.3V$  and  $T_A = 25^{\circ}C$ .

Note 4: f = 1 MHz,  $t_r$  and  $t_f \le 6$  ns.

Note 5: ESD Rating: HBM (1.5 k $\Omega$ , 100 pF) all pins  $\geq$  2000V.

EIAJ (0 $\Omega$ , 200 pF)  $\geq$  250V

## **Parameter Measurement Information**

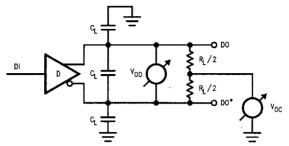


FIGURE 1. V<sub>OD</sub> and V<sub>OC</sub> Test Circuit

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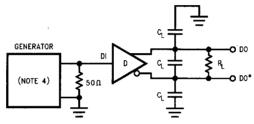


FIGURE 2. Driver Propagation Delay Test Circuit

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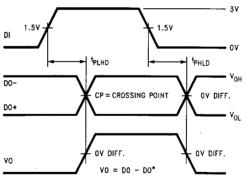


FIGURE 3. Driver Differential Propagation Delay Timing

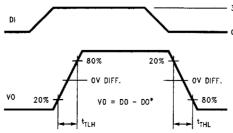


FIGURE 4. Driver Differential Transition Timing

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# Parameter Measurement Information (Continued)

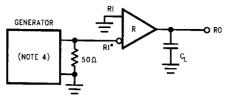


FIGURE 5. Receiver Propagation Delay Test Circuit

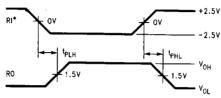


FIGURE 6. Receiver Propagation Delay Timing

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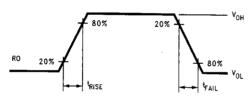


FIGURE 7. Receiver Rise and Fall Times